

Magnetic and electronic structures of nanographene and fluorinated nanographene with an interplay of edge-state spins and dangling bond spins

Toshiaki Enoki

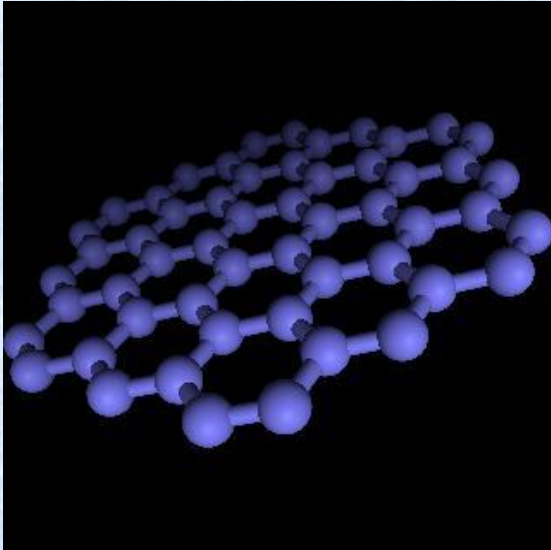
*Department of Chemistry
Tokyo Institute of Technology*



graphene

April 10-13, 2012 · Brussels (Belgium)

graphene



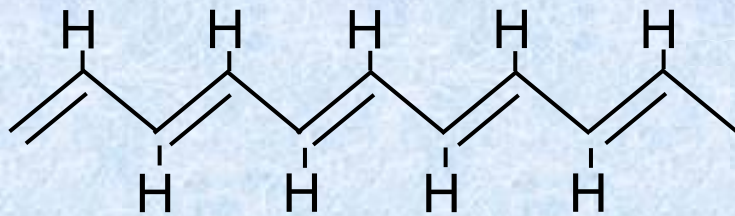
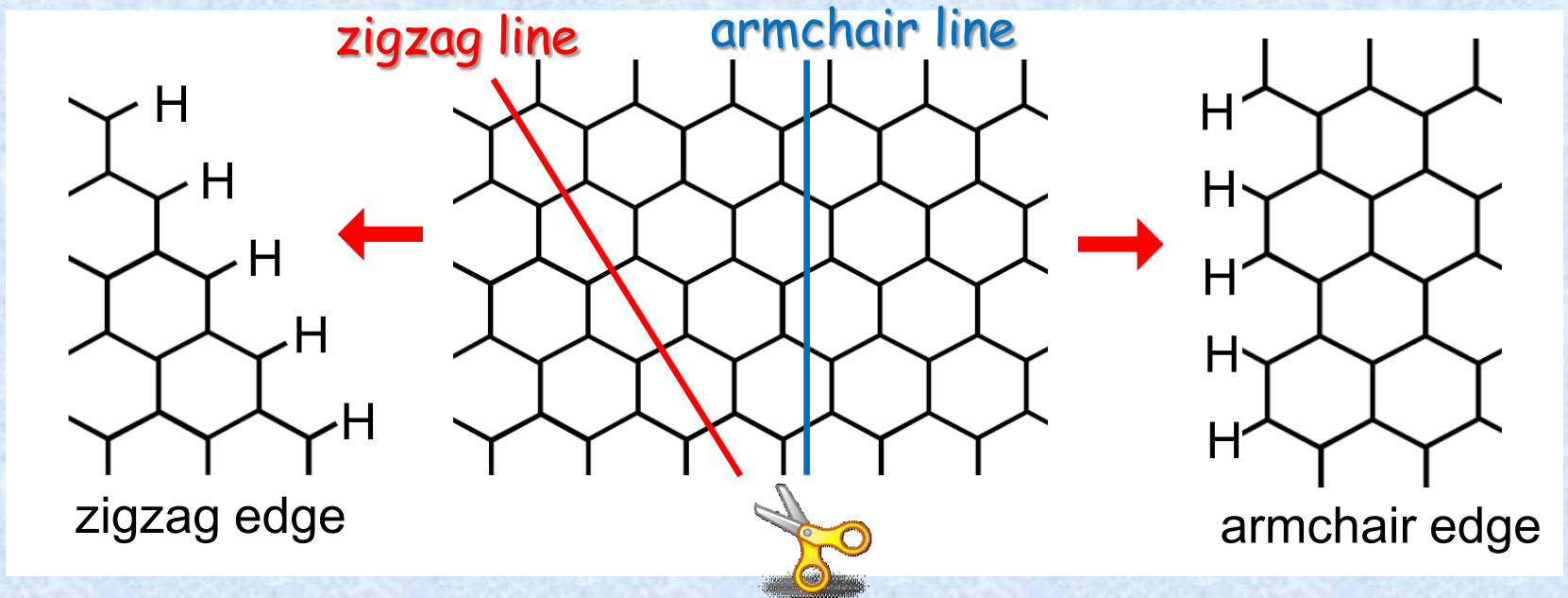
nanographene

open edge
magnetic properties

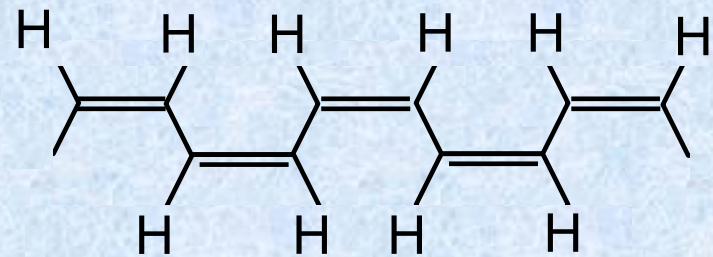


polycyclic aromatic molecules

T. Enoki, *Physica Scripta T146*, 014008 (2012).



trans-polyacetylene



cis-polyacetylene

Edge modifies the electronic structure in two manners

edge shape dependent (zigzag/armchair)

electron scattering/interference at the edge

superlattice pattern (STM)

Raman G-band (C-C stretching; 1600 cm^{-1})

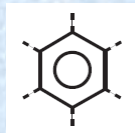
localized non-bondings π state at the edge (edge state)



graphene and edge effect for chemists and physicists

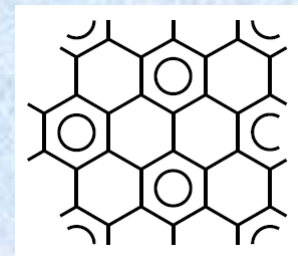
chemistry aspect aromaticity

Clar's aromatic sextet rule



aromatic sextet

graphene



aromaticity 1/3
chemically active

physics aspect

massless Dirac fermion (relativistic wave equation)
in the bipartite lattice

zero-gap semiconductor
with linear bands ($\propto \mathbf{p}$)

$$\mathcal{H} = v_F \sigma \mathbf{p}$$

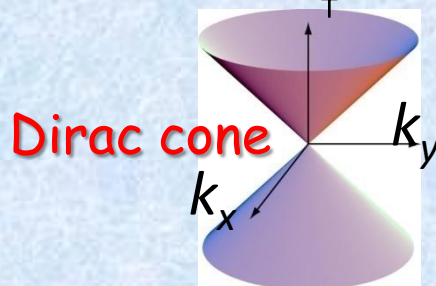
momentum \mathbf{p}

Fermi velocity $v_F \approx (1/300)c$

pseudo-spin $\sigma \uparrow \downarrow$

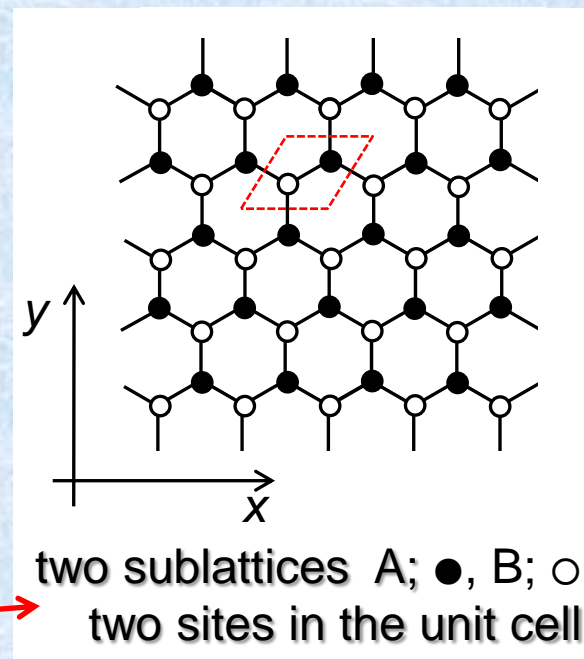
degree of freedom; 2

conduction band

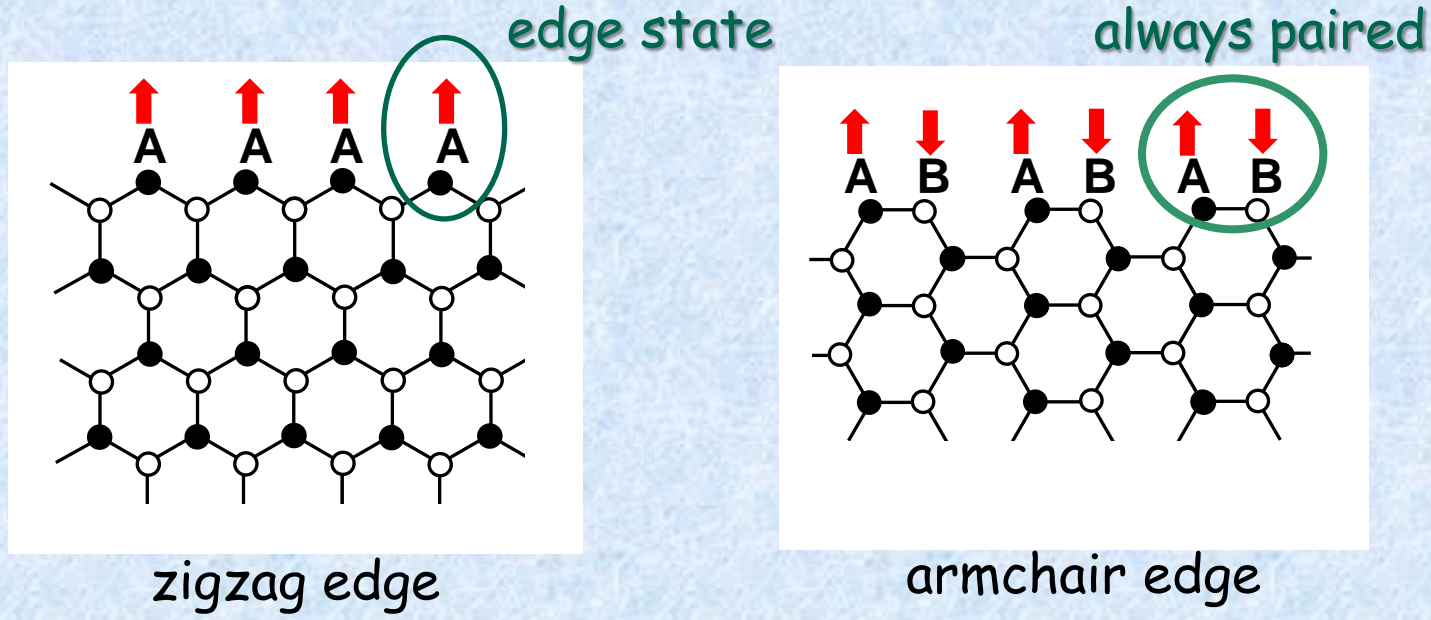


Dirac cone

valence band



How physicists understand the edge state



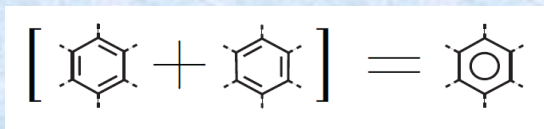
edge state (magnetic)

only one of the sublattices (A, B) exists in the zigzag edge
broken symmetry of the pseudo-spin \uparrow in Dirac fermion

Clar's aromatic sextet rule (# of sextets) most stable structure

maximal number of the sextets separated by the entirely empty rings

well stabilized

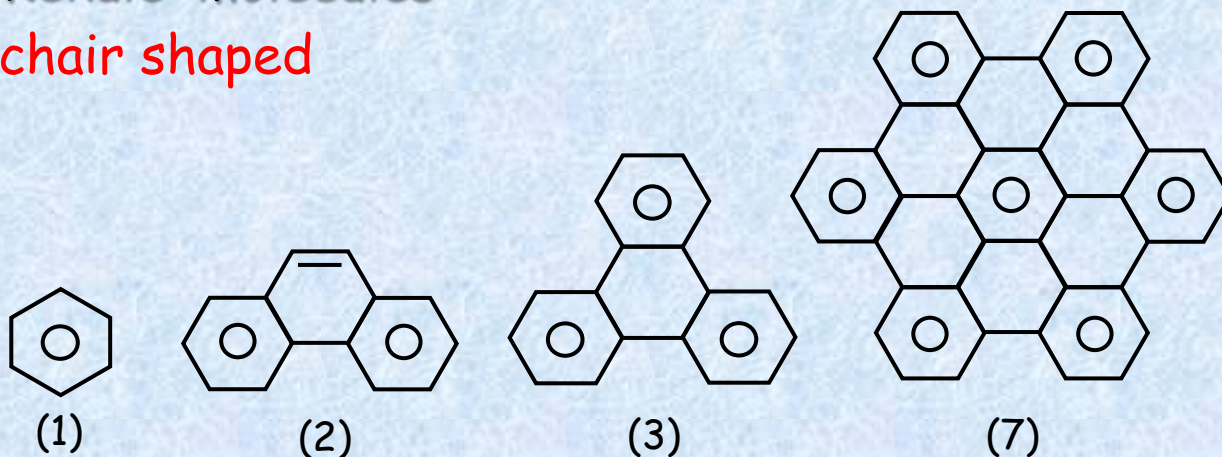


sextet

benzene ring with C atoms
singly bonded to the surrounding

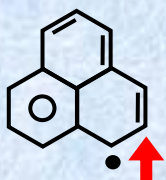
aromatic Kekulé molecules

armchair shaped

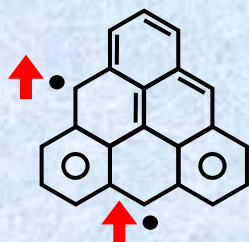


non Kekulé molecules (non-bonding π -state (π -radical))

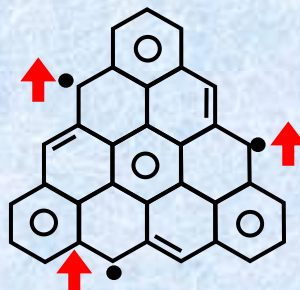
zigzag shaped



$S=1/2$
(1)



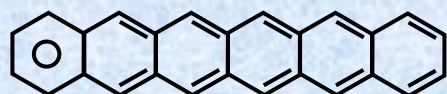
$S=1$
(2)



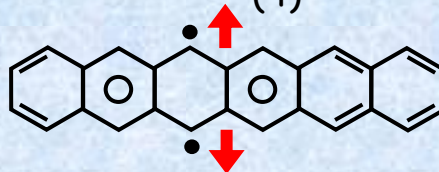
$S=3/2$
(4)

less stabilized
ferromagnetic

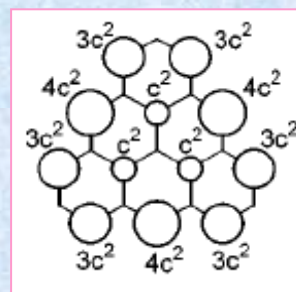
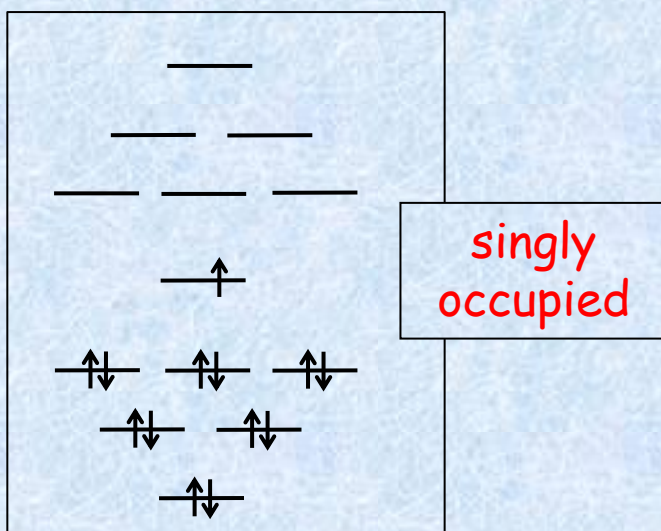
Hund rule



(1)



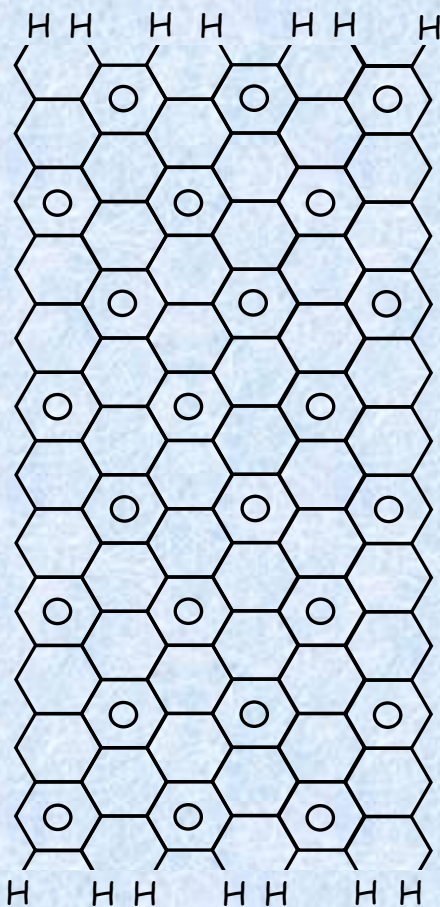
less stabilized
antiferromagnetic
(open shell singlet)



localized around
zigzag edges

edge state

nanographene ribbon

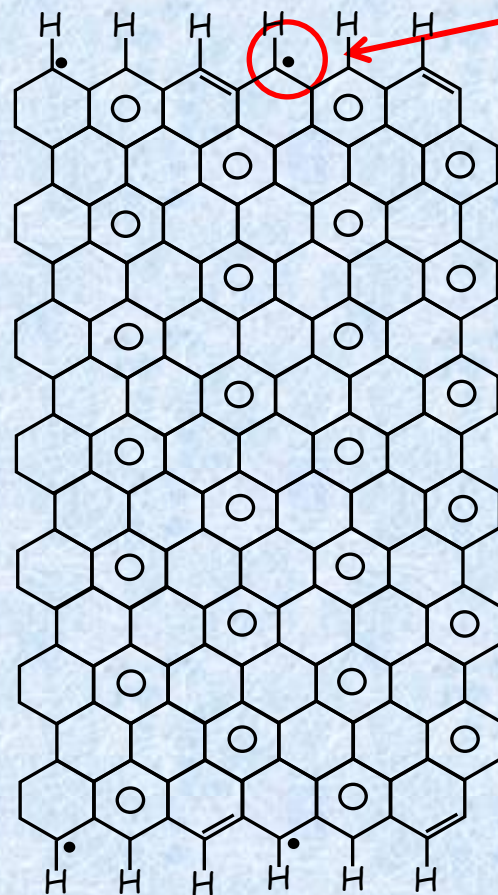


armchair edge

same to infinite graphene

nonmagnetic

Clar's sextet formula



radical spins at
zigzag edges
magnetically
electronically
chemically
active

$$\sqrt{3} \times \sqrt{3}$$

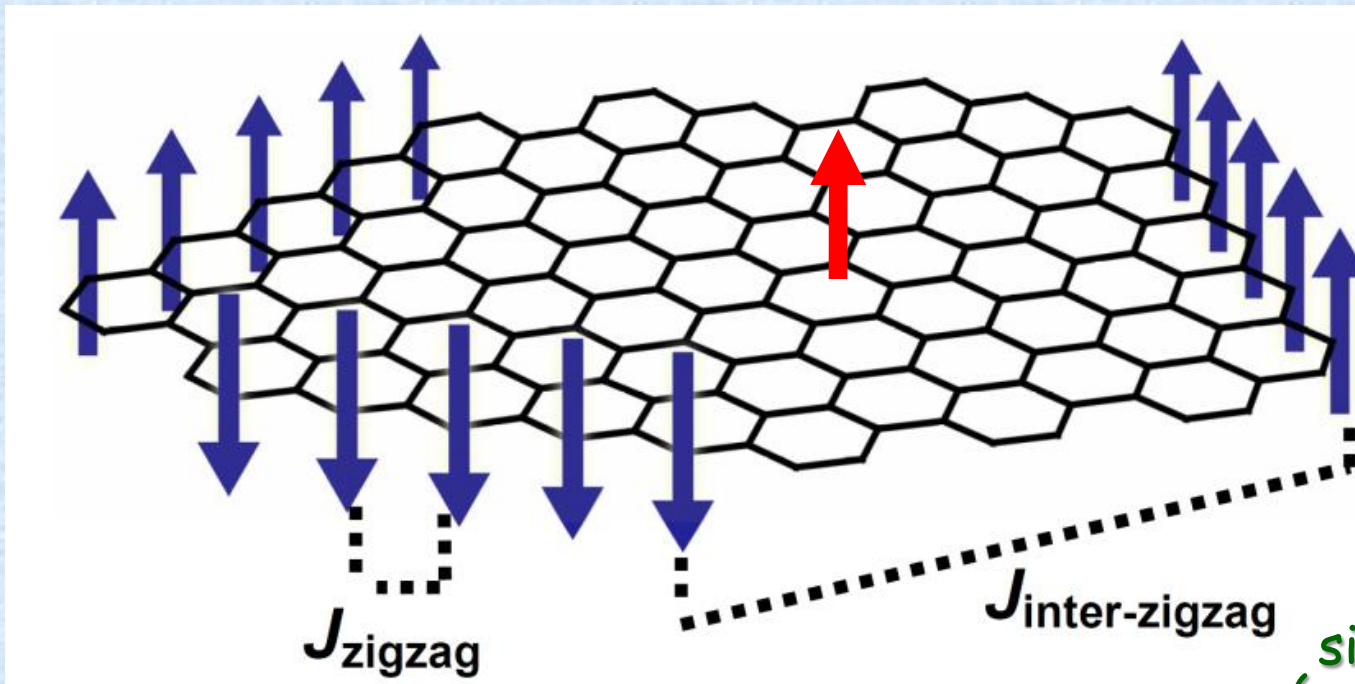
superlattice
in the interior

zigzag edge

magnetic (edge-state spins)

detailed magnetic structure in a nanographene sheet

isotropic Heisenberg spin (small spin-orbit interaction ($\sim 5 \text{ cm}^{-1}$) of C atom)



inter-zigzag int.
similar to RKKY int.
(conduction-electron-mediated)

$J_{\text{zigzag}} \sim \text{several } 10^3 \text{ K}$ ferromagnetic

$J_{\text{inter-zigzag}} \sim 10^{-1} - 10^{-2} J_{\text{zigzag}}$ ferro- or antiferromagnetic
depending on the geometrical relation

effective magnetic moment

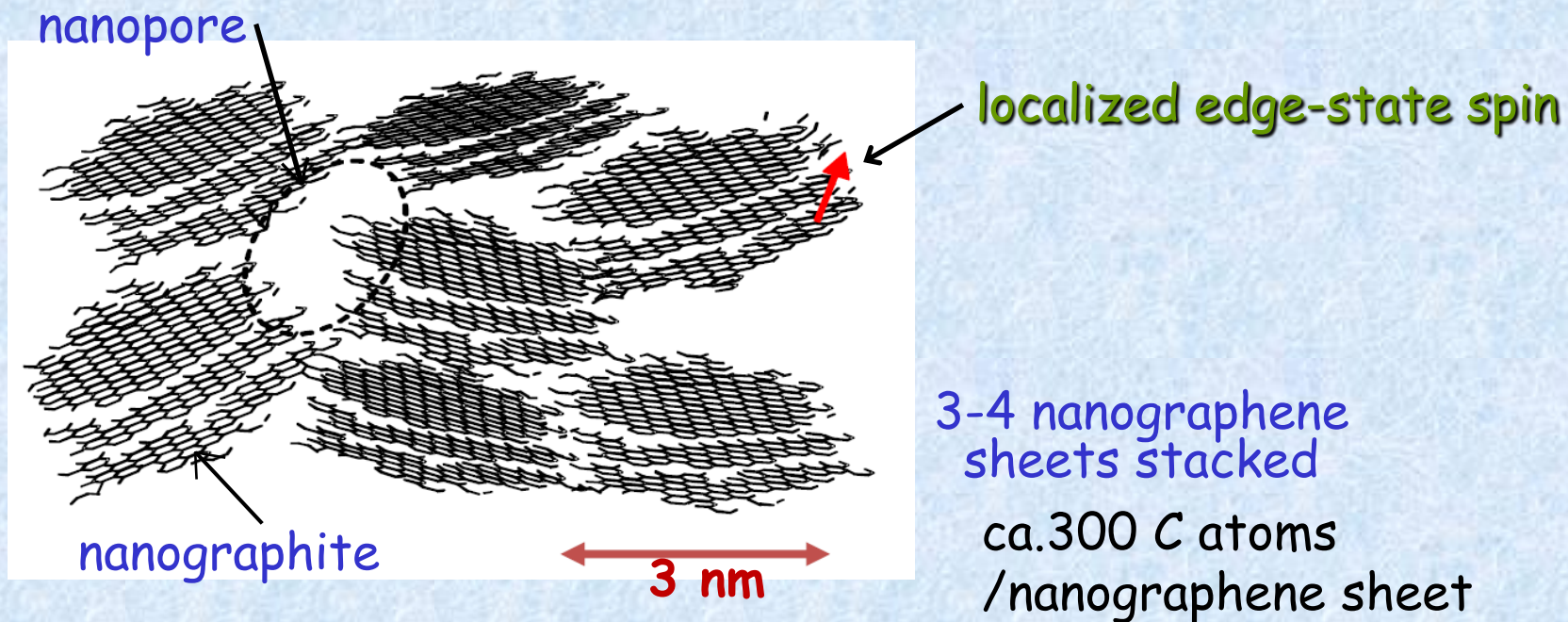
ferrimagnetic structure

electronic structure of edge state
of π -electron origin

NEXAFS & ESR

Joly, Kiguchi, Terrones, Dresselhaus, Takai, Enoki, et al. *Phys. Rev.* **B81**, 245428 (2010)

Our target **activated carbon fiber (ACF)**
nanographene-based nanoporous carbon



3D random network of nanographite domains
soft and flexible network

nanopores

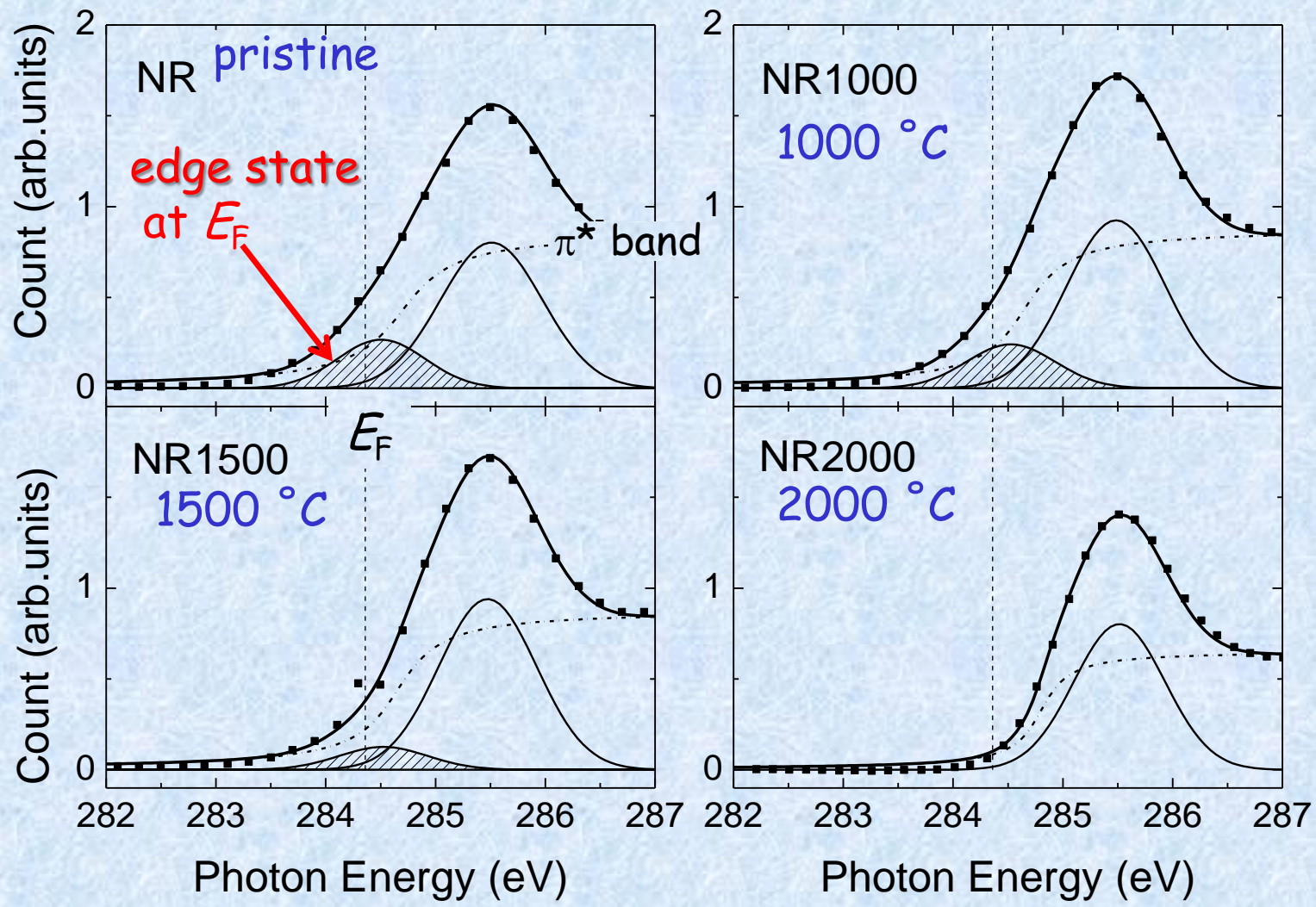
adsorption of guest molecules

edge-state spins

spin concentration expected from Clar's rule

NEXAFS (near edge x-ray absorption fine structure)
 graphene nanoribbon **C 1s to π^* peak under different annealing conditions**

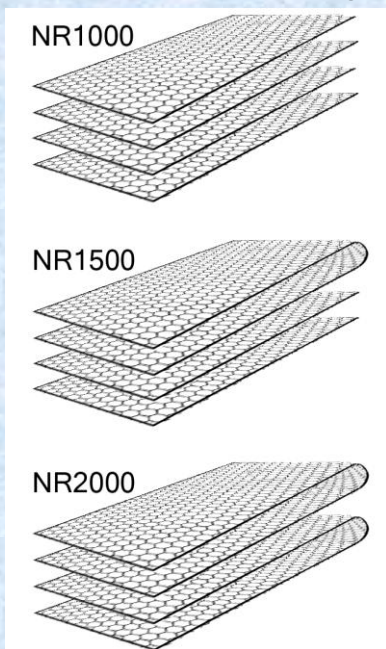
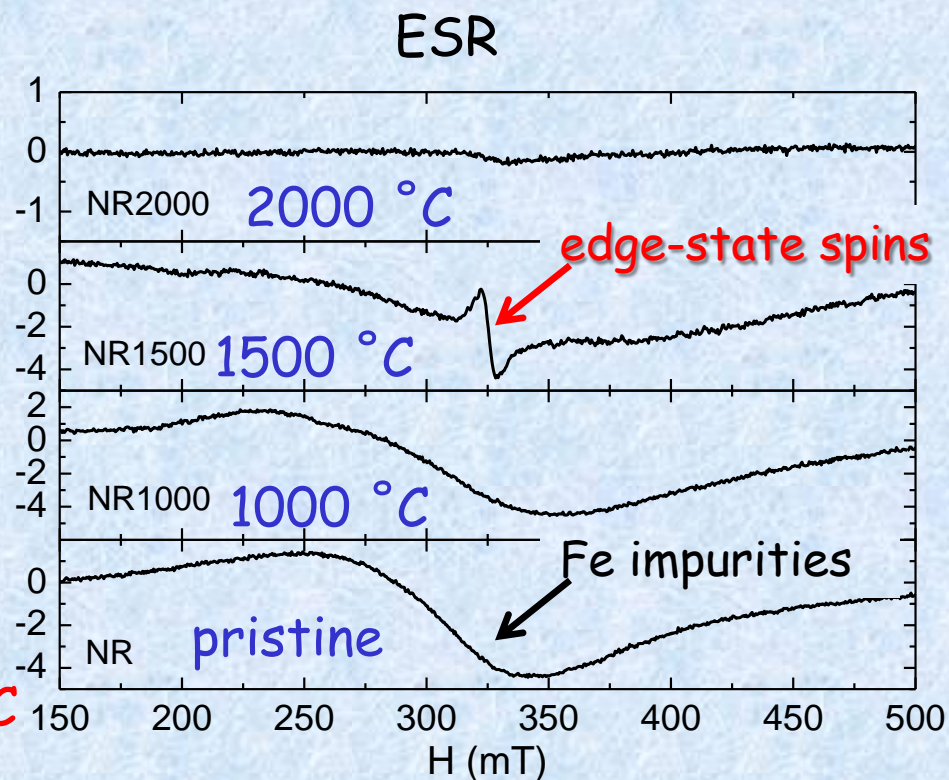
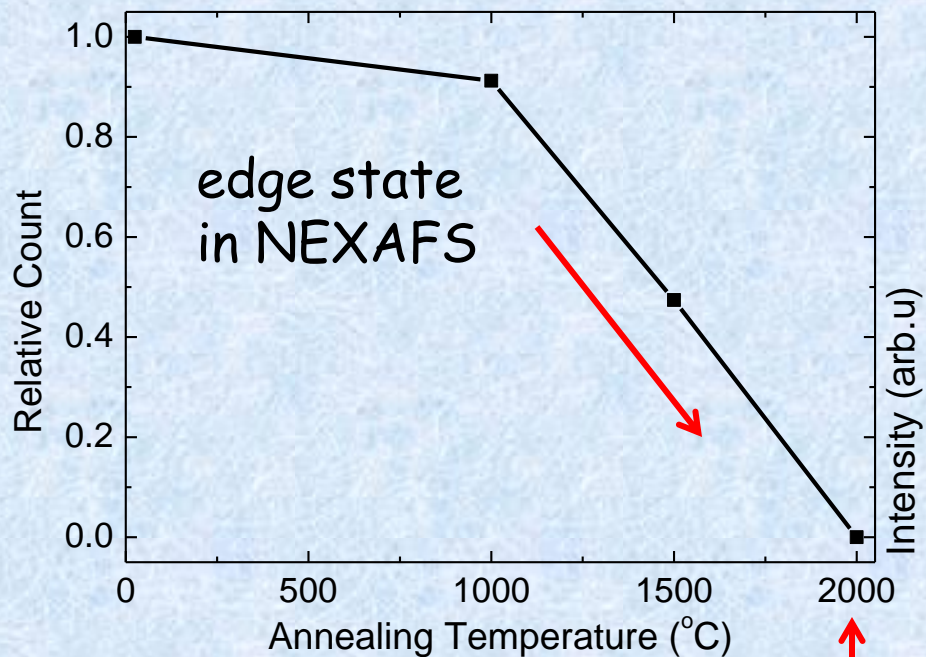
Joly, Kiguchi, Terrones, Dresselhaus, Takai, Enoki, et al. *Phys. Rev.* **B81**, 245428 (2010)



edge state decreases with HTT and disappears at HTT=2000 °C

heat treatment above 2000 °C (> graphitization temperature)

edge state contribution in the C 1s to π^* vs ESR intensity



loop formation
edge disappears

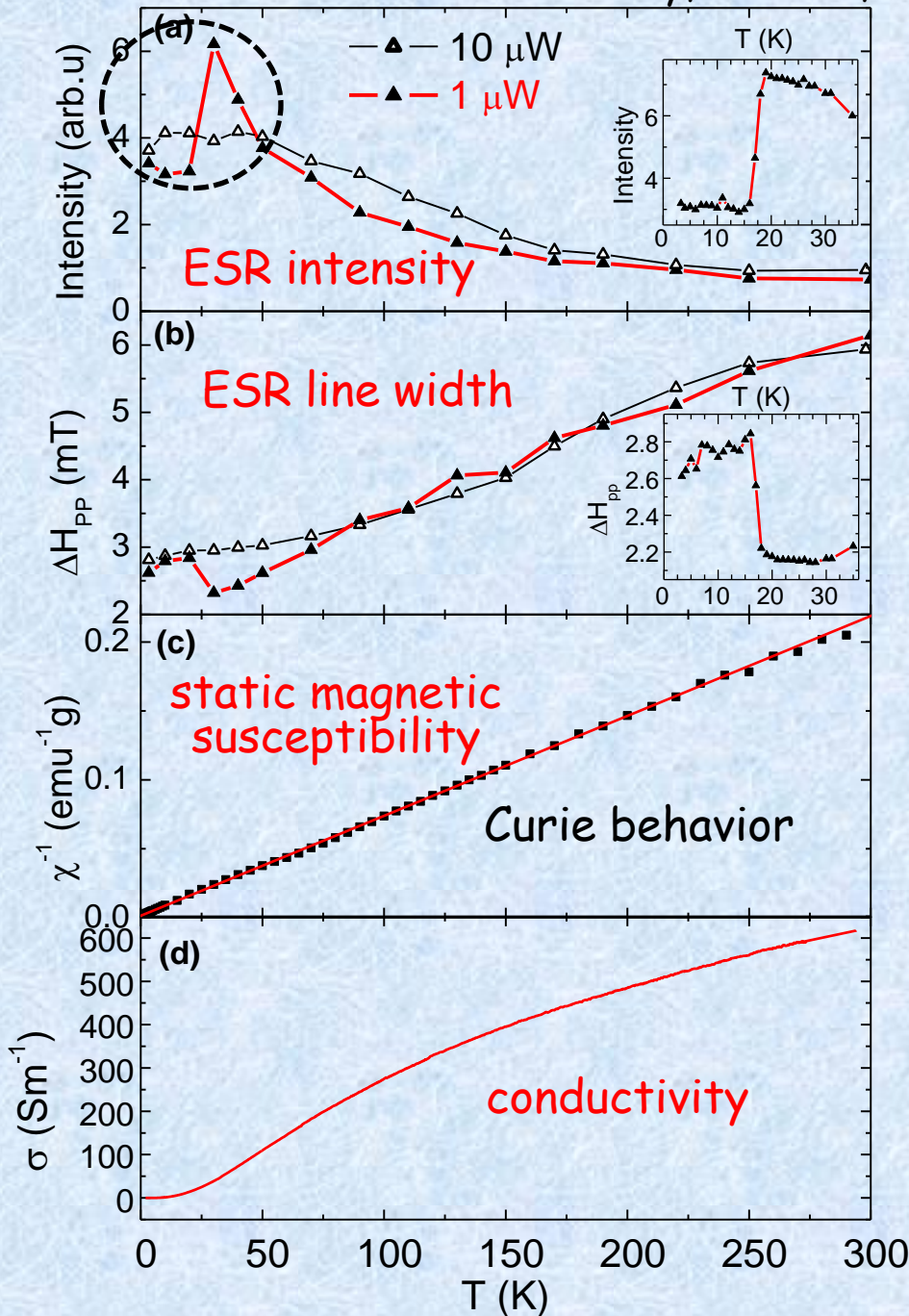
no edge state

edge state is magnetic

magnetic structure of edge-state spin system

V. L. J. Joly, K. Takai, T. Enoki, et al., *Phys. Rev. B* **81**, 115408 (2010)

T. Enoki, *Many Facets of Graphene*, VCH, (2012), in press



dynamical behavior
of the edge-state spin system
by ESR and electron transport
investigations

ESR intensity
Curie type behavior of edge-state spins
down to ca.30 K

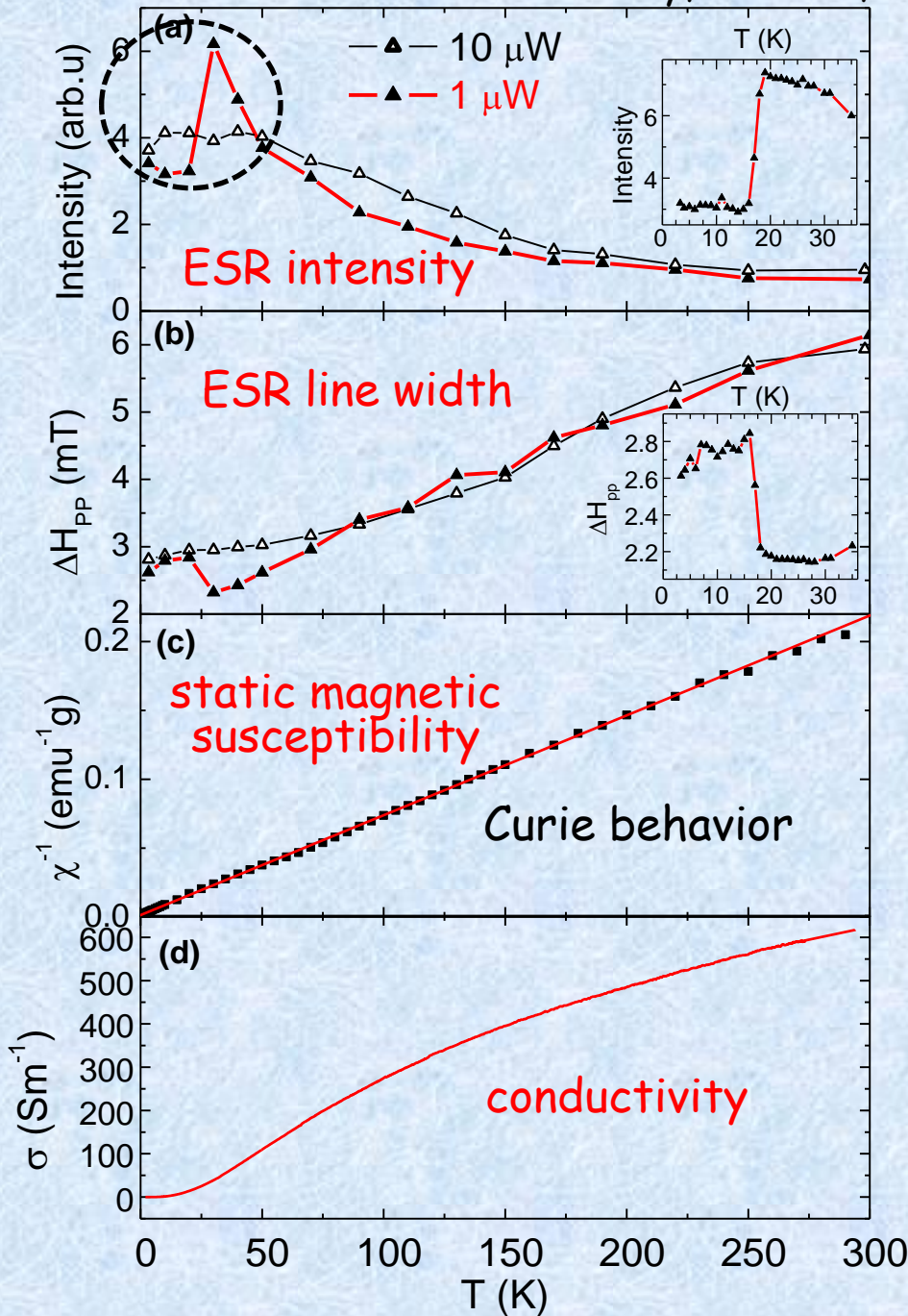
drops below 30 K
in disagreement with the static
susceptibility

ESR line width
linear decrease
with the lowering of the temperature
down to ca.30 K

upsurge below ca.30 K

microwave power dependence

dynamical process governs



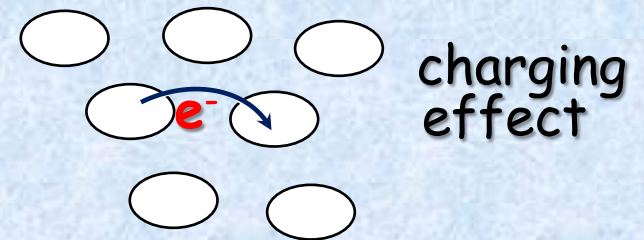
dynamical behavior
of the edge-state spin system
by ESR and electron transport
investigations

dynamical process governs

conductivity decreases
with lowering of the temperature

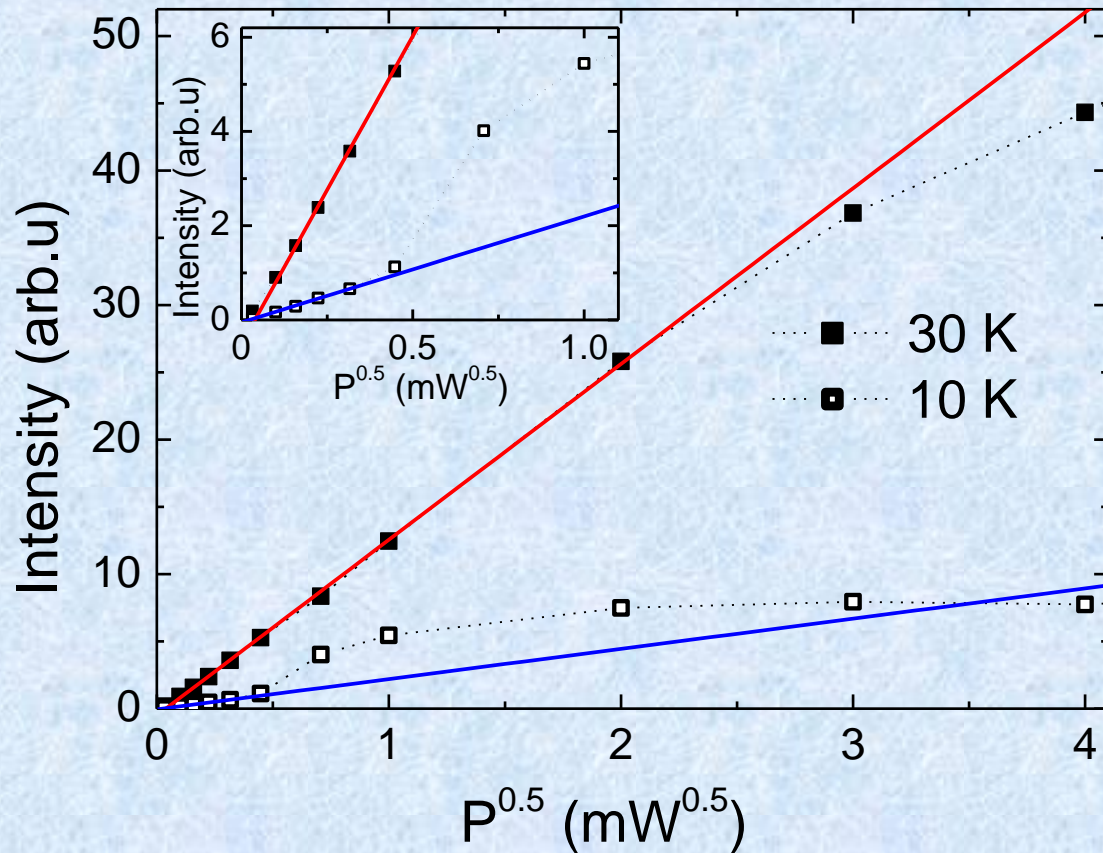
Coulomb-gap variable range hopping
inter-nanographite-domain transport

$$\sigma \propto \exp\left[-(T_0/T)^{1/2}\right]$$



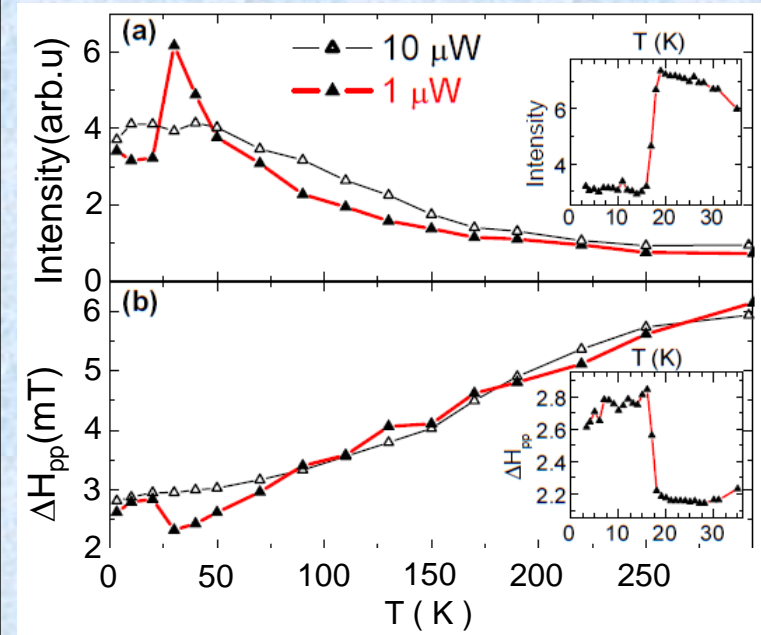
electron localization at low T

ESR saturation curves (intensity vs $\sqrt{\text{microwave power}}$)



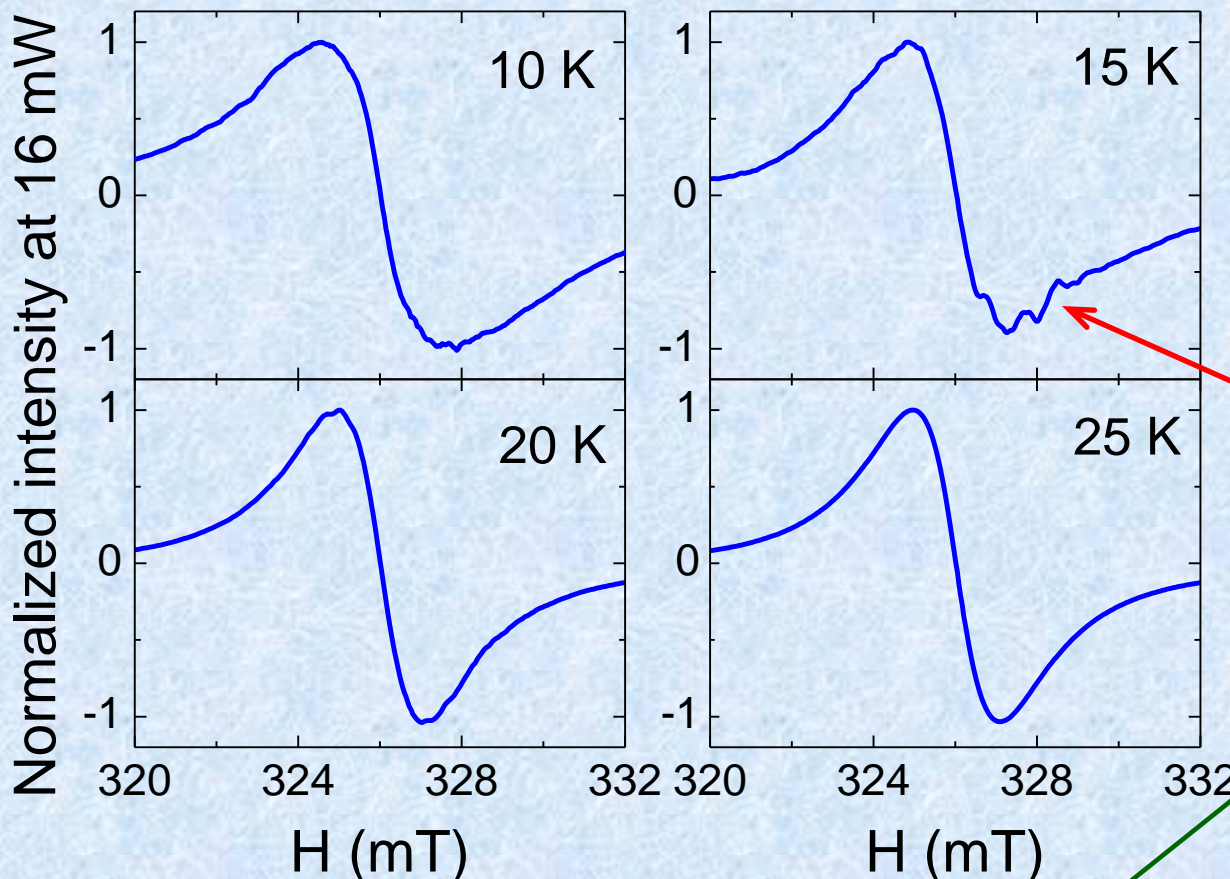
$T > 30$ K
less saturated

$T < 30$ K
strong saturation



inhomogeneous spin state
in the low temperature regime ($T < 30$ K)

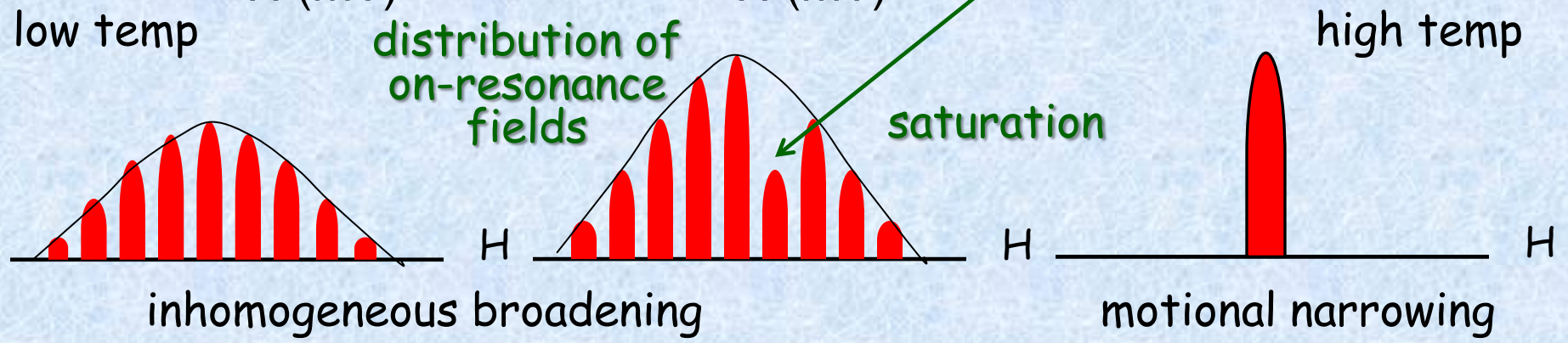
ESR line shape at high microwave power (16 mW)



sharp Lorentzian
 $T > 30$ K

deviation from Lorentzian
 $T < 30$ K

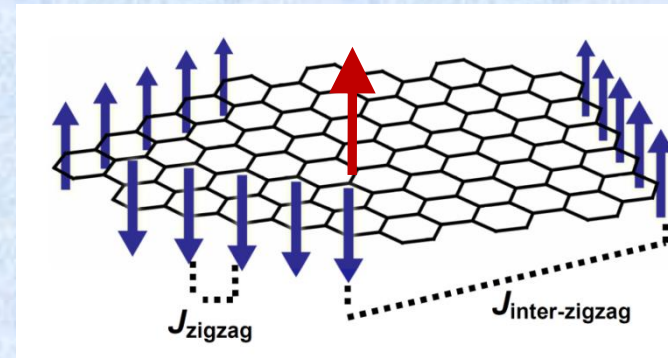
hole burning behavior
in the high microwave
power range



nanographene/nanographite domain

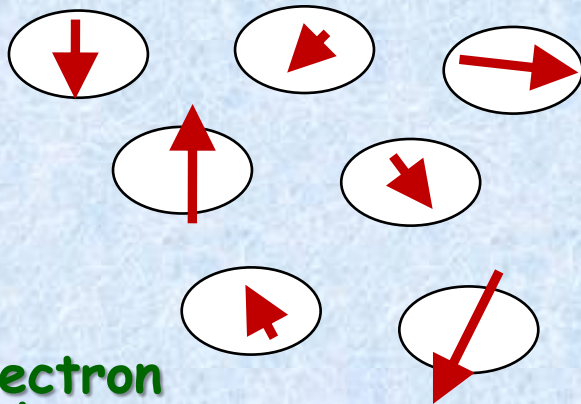
ferrimagnetic

a non-zero magnetic moment
with its value varying randomly

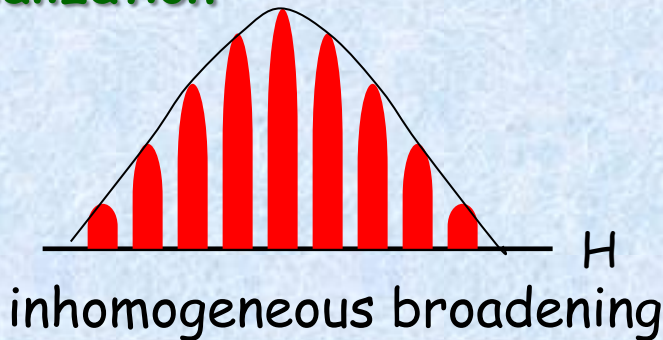


distribution of on-resonance fields

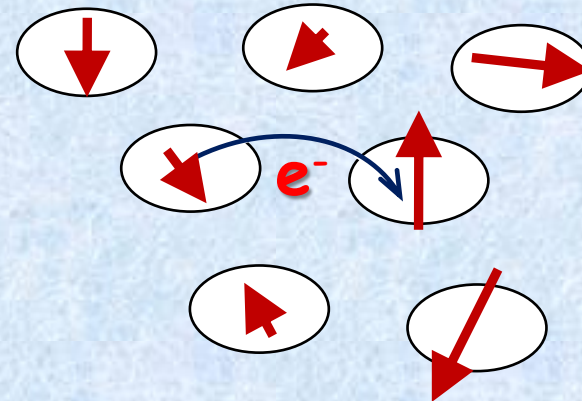
low temp



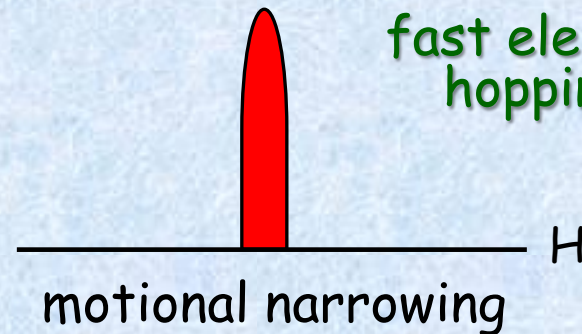
electron
localization



high temp

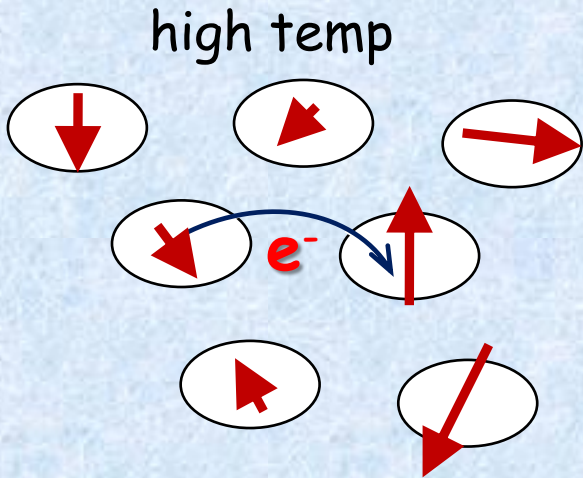


fast electron
hoppings



nanographene/nanographite domain

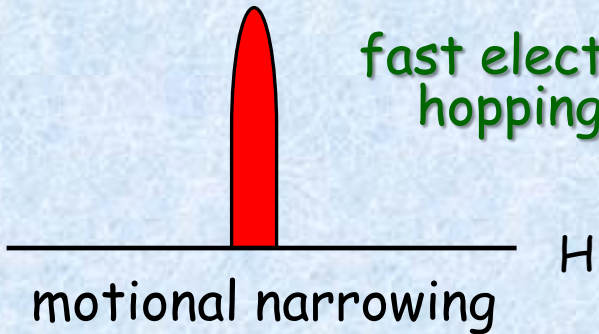
ferrimagnetic
a non-zero magnetic moment with its value varying randomly



inhomogeneous broadening at low T



important evidence of ferrimagnetic structure with varying net magnetic moments



each nanographite domain behaves as independent superparamagnetic particle in **electron localization state** at low T

behavior at high temperature
 $T > 30$ K

ESR signal

motional narrowing

intrinsic information on the
 individual nanographene

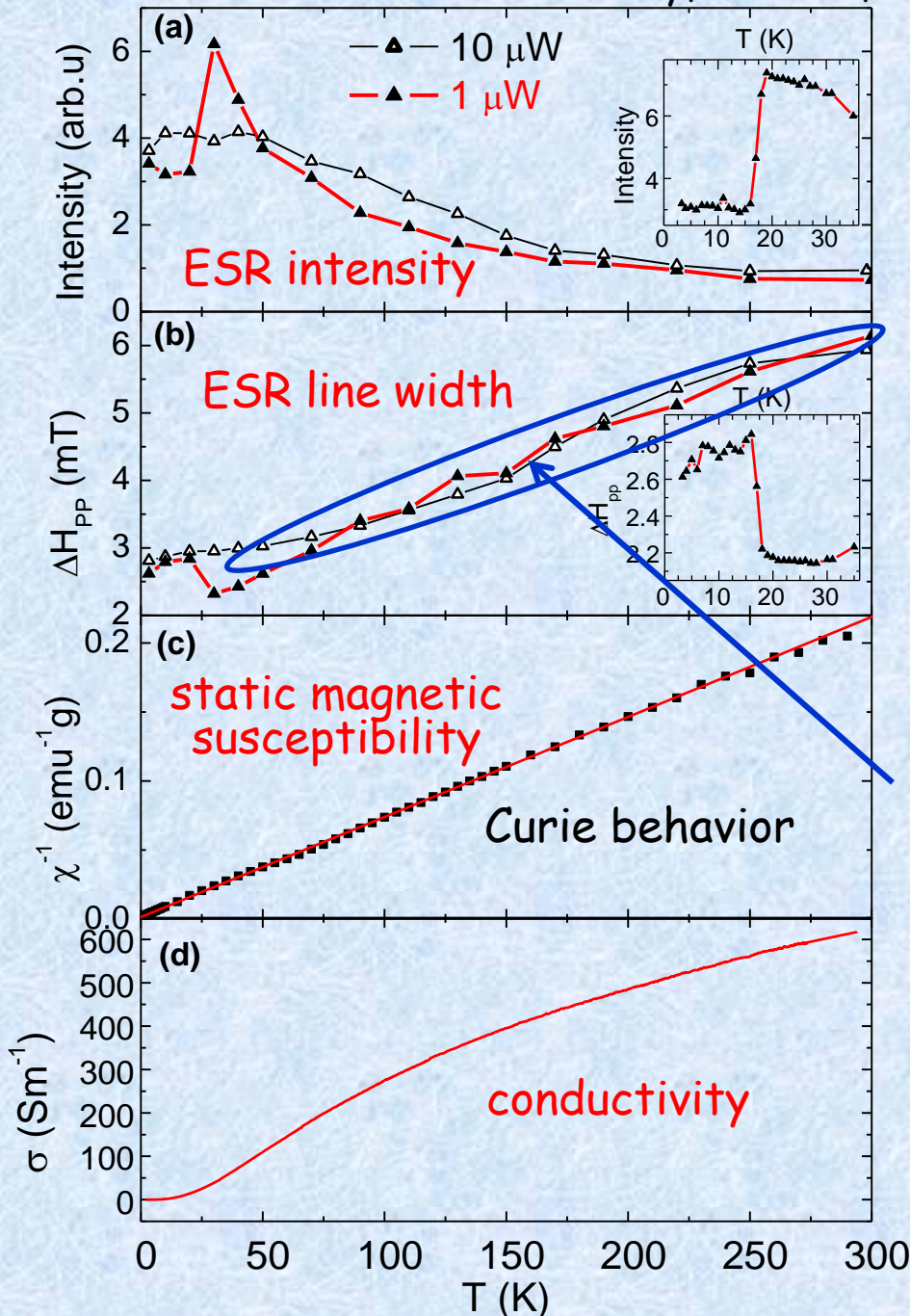
high $T (> 30$ K) linear T dependent ΔH

$$\Delta H \propto \frac{1}{T_{\text{edge-}\pi}} = \left(\frac{4\pi}{\hbar} \right) J_{\text{edge-}\pi}^2 D(\varepsilon_F)^2 k_B T$$

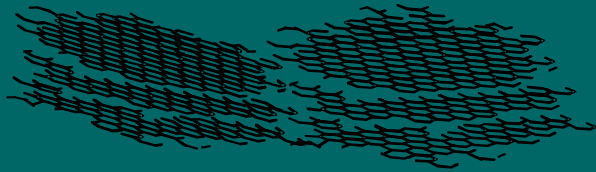
Korringa relation

$J_{\text{edge-}\pi}$ exchange interaction

edge-state spin & cond. carrier coupled

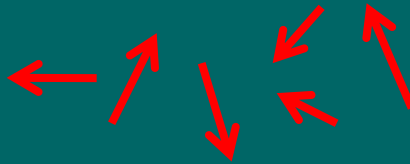


What happens in the magnetism
when heat treated ?



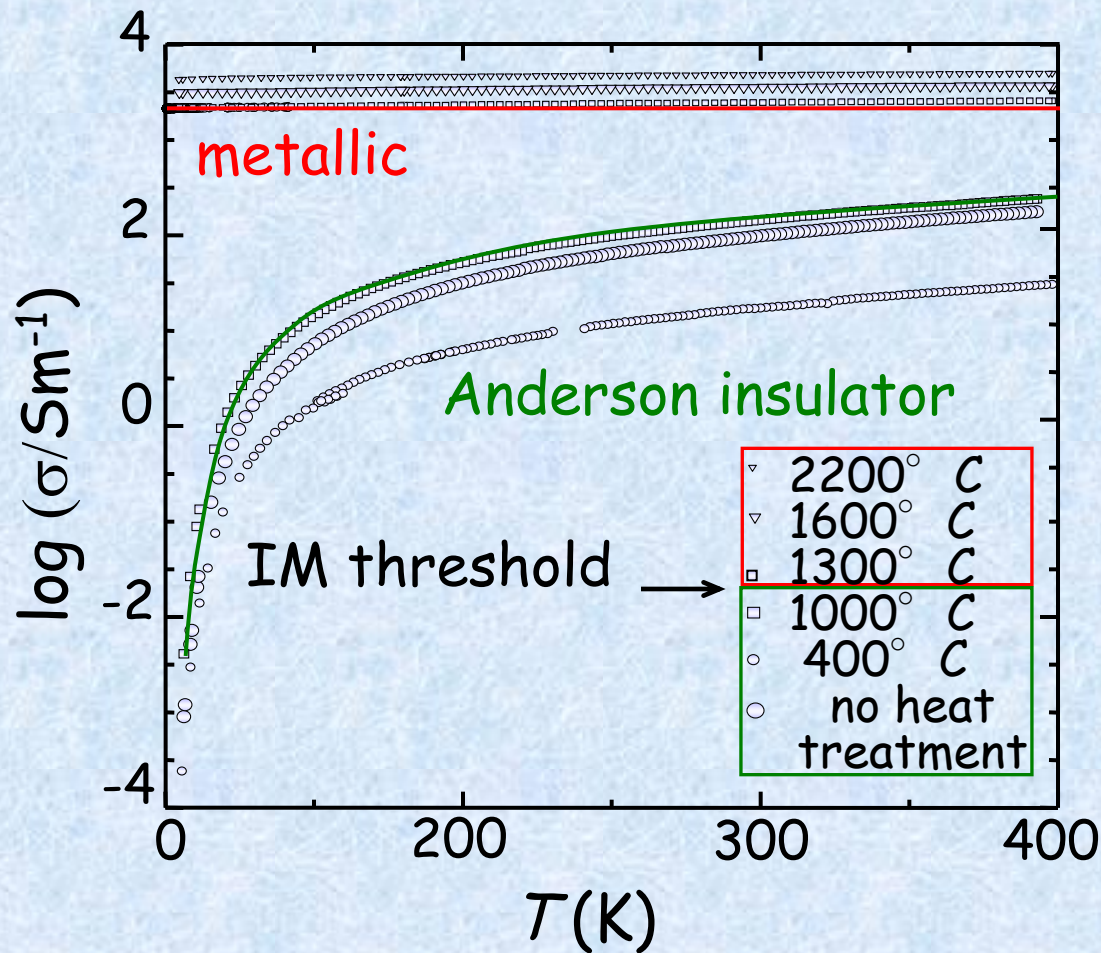
inter-nanographene
interaction strengthened

spin glass



Y. Shibayama, T. Enoki, et al. *Phys. Rev. Lett.* **84**, 1744 (2000).

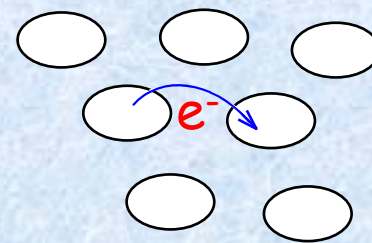
heat-treatment effect on conductivity



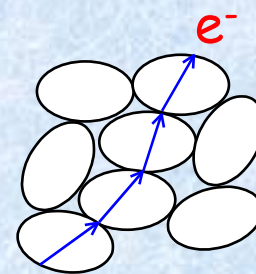
insulator-metal transition

inter-nanographite-domain interaction enhanced by heat-treatment

percolation threshold P_c
→ ca. HTT 1200° C

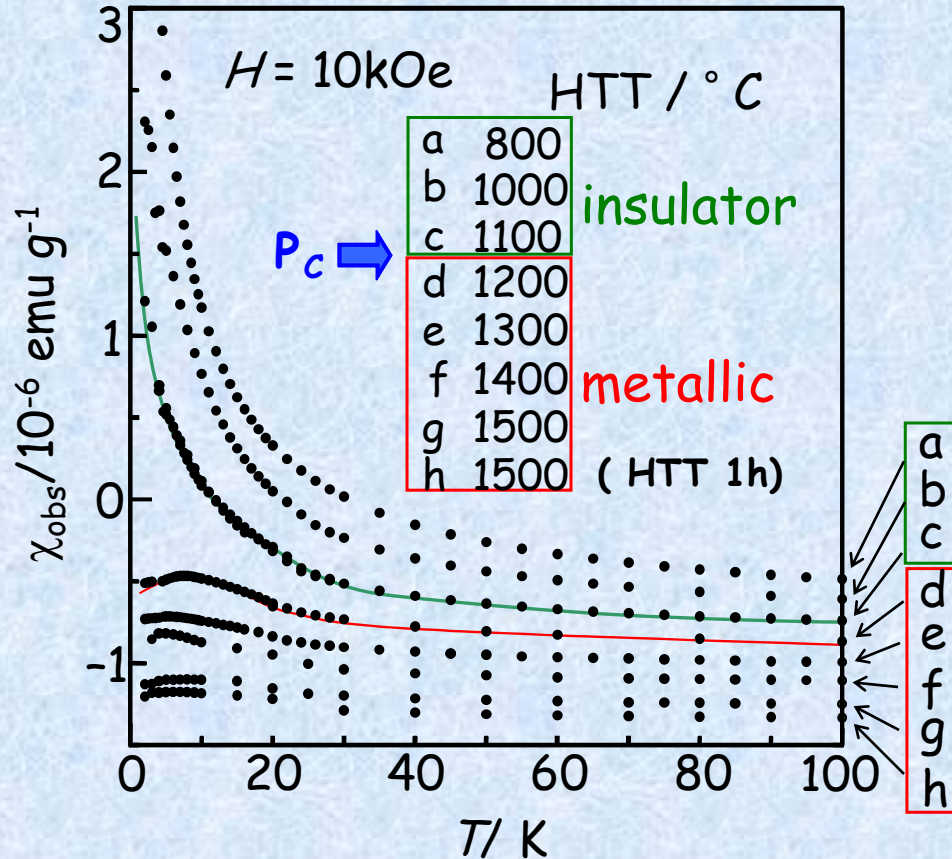


hopping



metallic

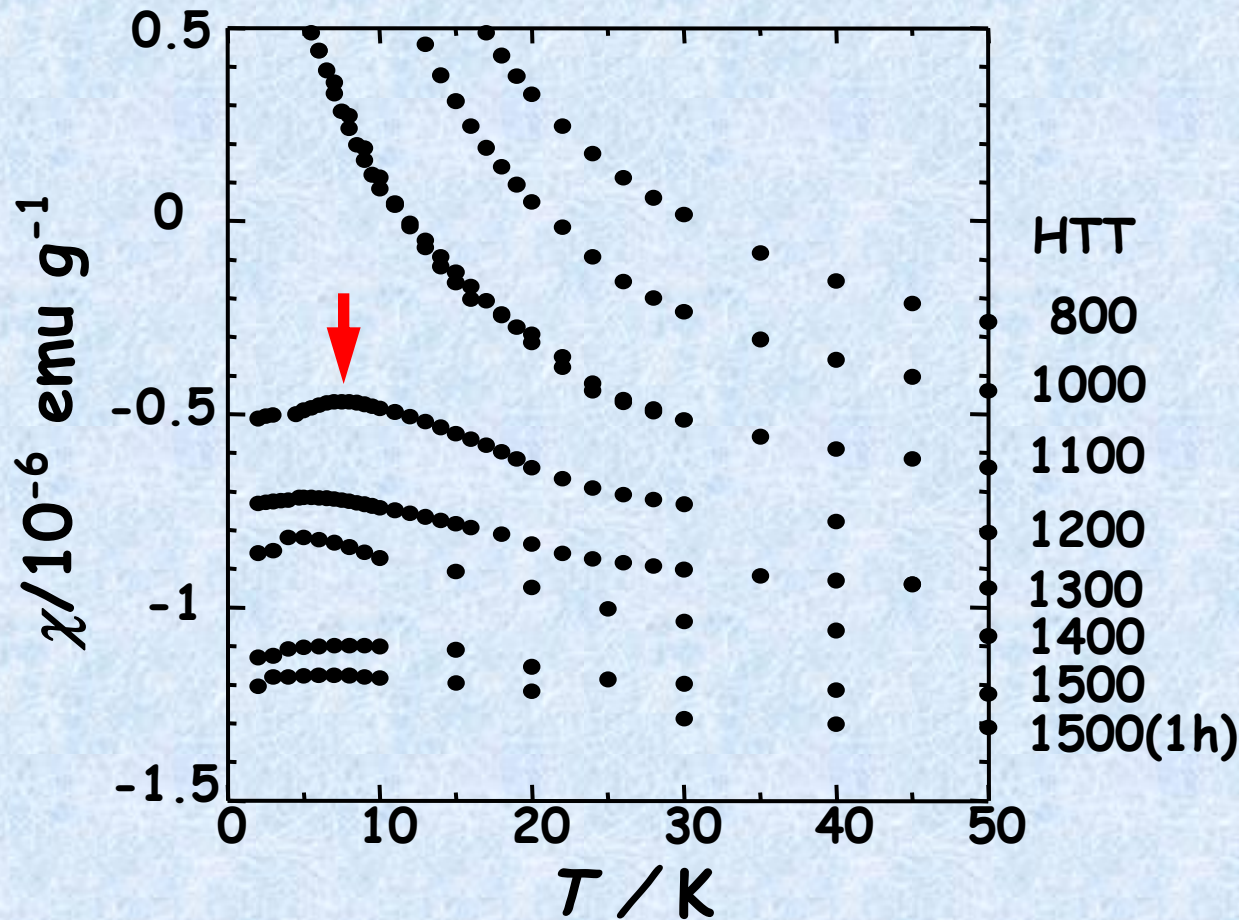
heat-treatment effect on magnetic susceptibility



HTT < P_c
Curie-Weiss behavior
with **localized spins**
and **negative Weiss**
temperature

HTT > P_c
less temp. dependent
enhanced diamagnetism

magnetism around the percolation threshold region

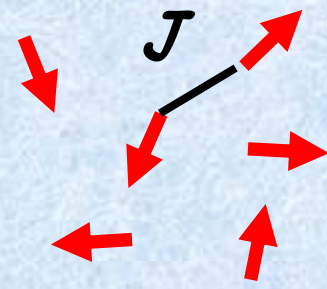
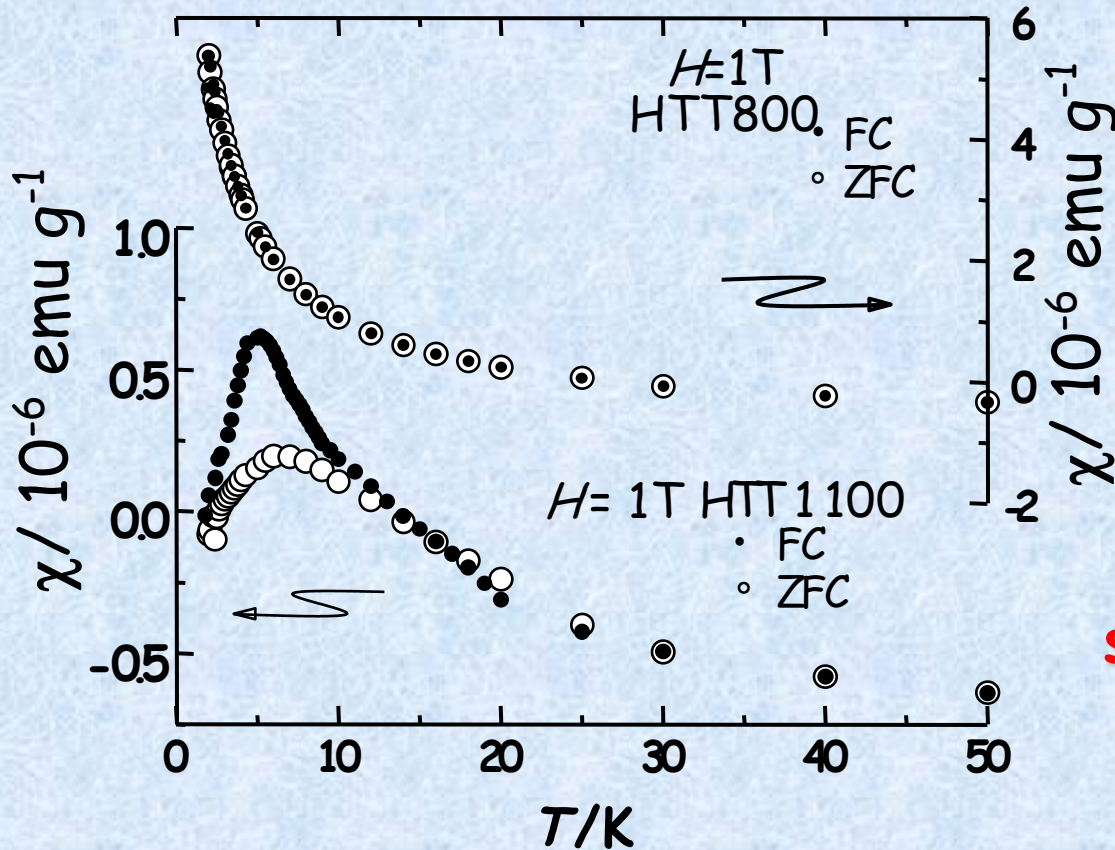


susceptibility peak $\sim 7\text{K}$

antiferromagnetic ordering?
negative Weiss temperature

field cooling effect

large field cooling effect around the MI threshold



disordered magnetism
spin-glass-like behavior

exchange interaction
random distribution

$$|\sqrt{\langle \Delta J^2 \rangle} / \langle J \rangle| \sim 0.8$$

edge state of π -electron origin
topological origin from the pseudo-spin in Dirac fermion

σ -dangling bond
defect origin in the sp^3 backbone

What difference?

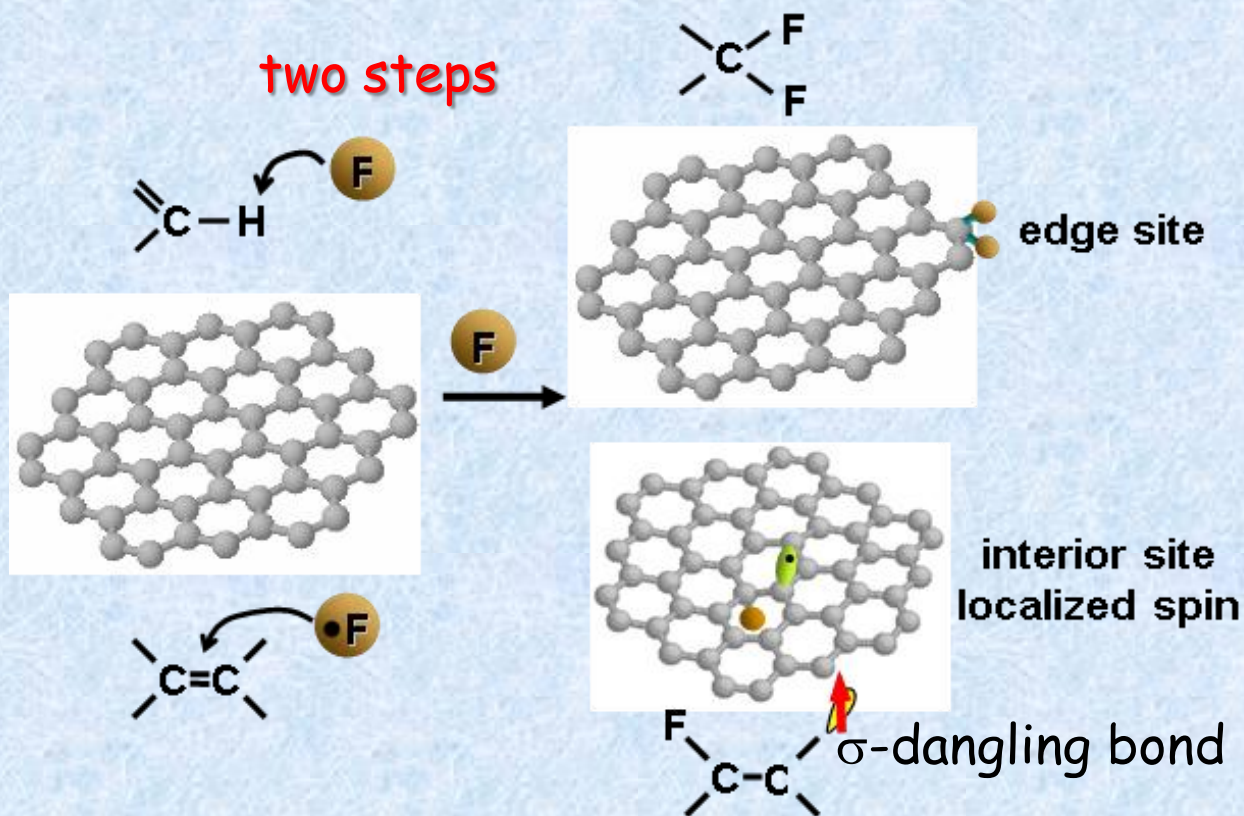
fluorination of nanographene

M. Kiguchi, V. L. J. Joly, K. Takai, T. Enoki, et al., *Phys. Rev. B* 84, , 045421 (2011)
T. Enoki, *Bull. Chem. Soc. Jpn.* 85, 249264 (2012)

fluorination of nanographene

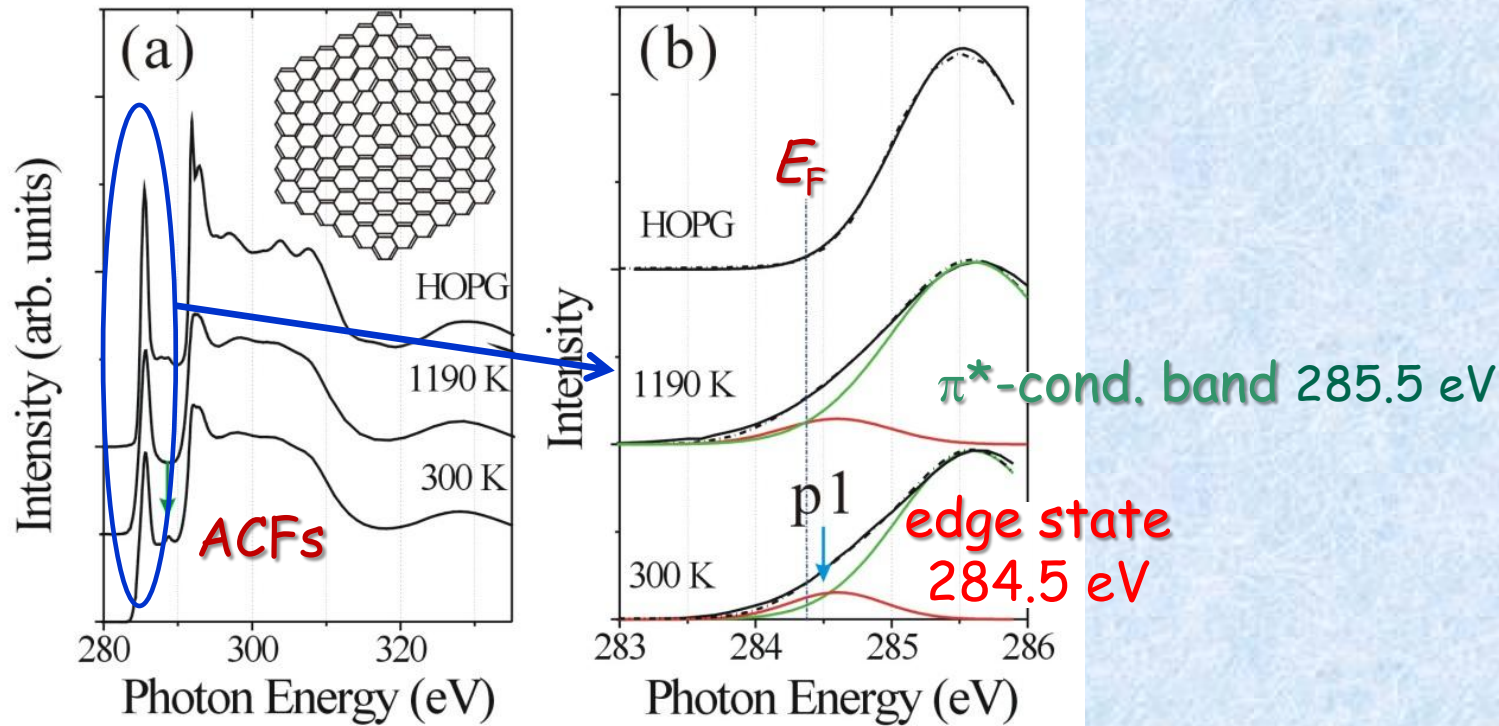
two kinds of nonbonding state having localized spin

edge state of π -electron
 σ -dangling bond of defect



electronic structure & magnetism

fluorination of nanographene

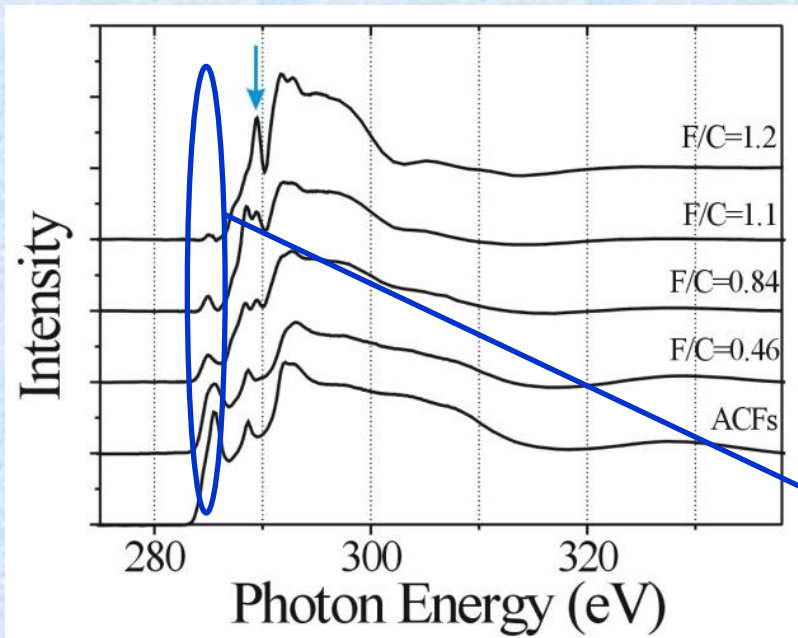


near edge X-ray absorption fine structure (NEXAFS)
nanographene in activated carbon fibers (ACF)

pristine ACFs heat-treated ACFs (1190 K)

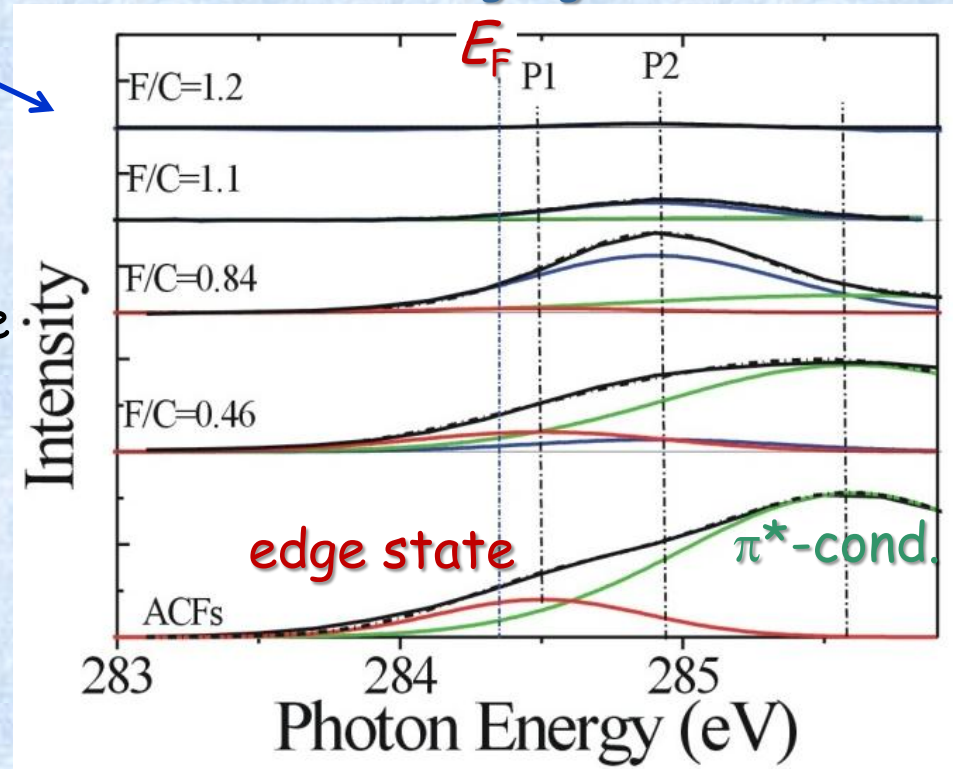
NEXAFS

fluorinated ACFs ($F/C = 0 - 1.2$)



σ -dangling bond state (284.9 eV)
appears independent from edge state
 $0.4 < F/C < 1.2$
with **a maximum intensity** at $F/C \sim 0.8$

σ -dangling bond state

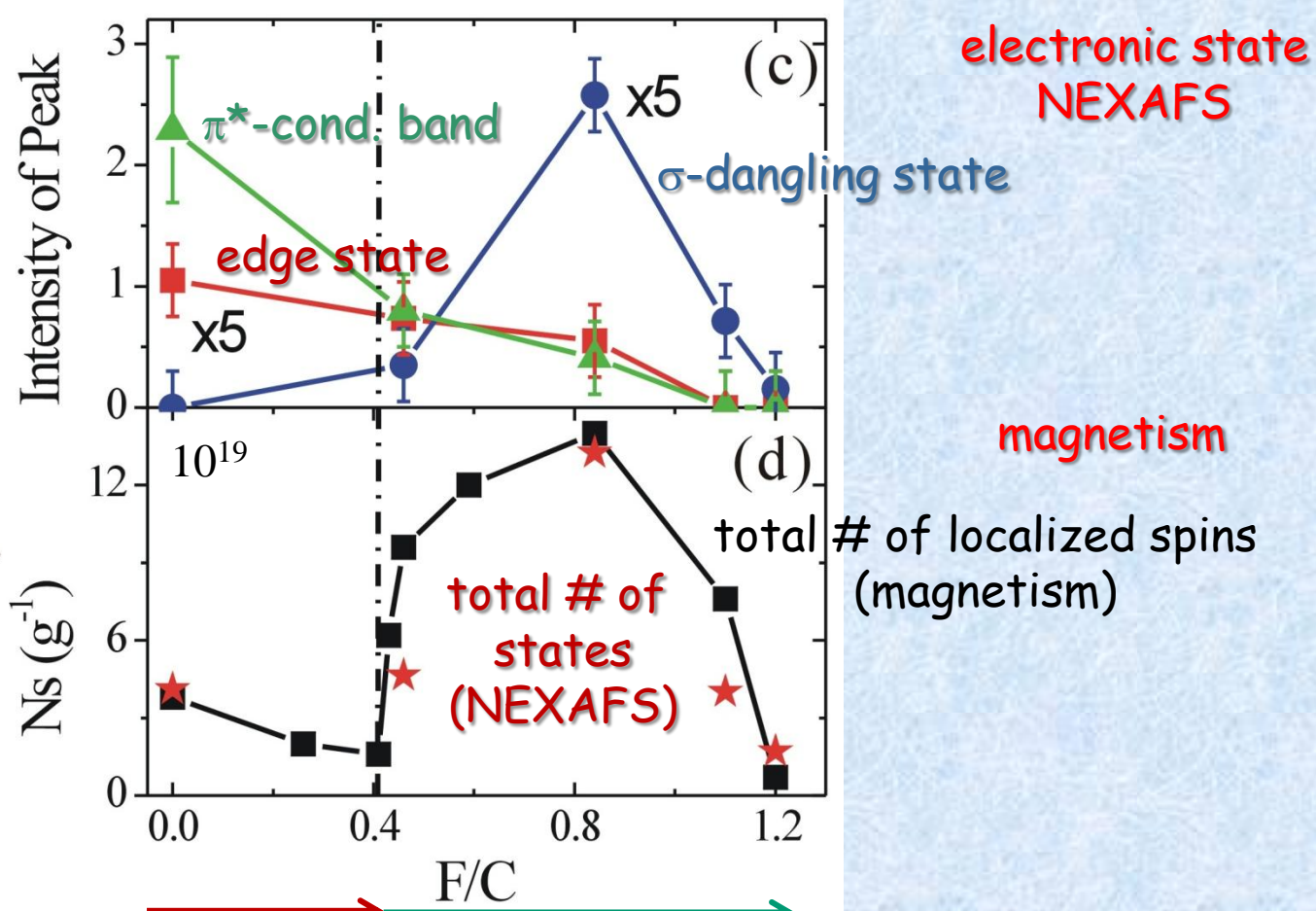
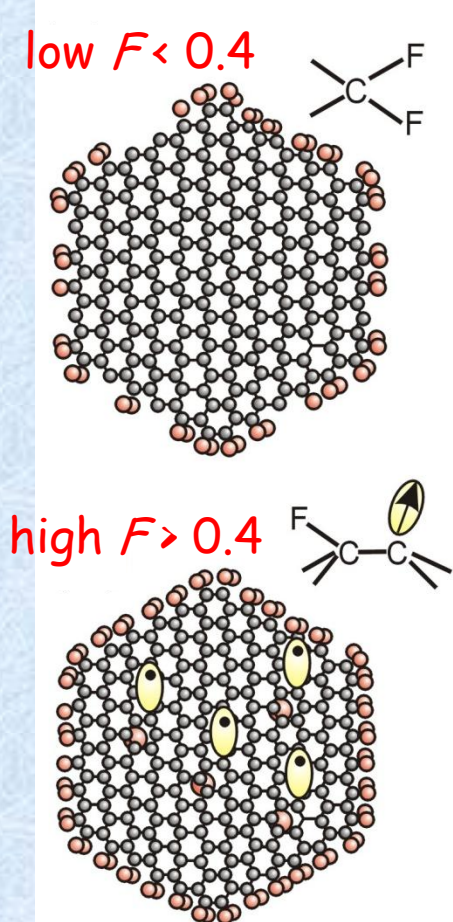


edge state of π -electron
chem. shift 284.5 eV more negative
from π^* conduction band
large screening effect
large local density of states

σ -dangling bond
chem. shift 284.9 eV less negative
weak screening effect

fluorine concentration dependence of NEXAFS intensity and localized spin

of Carbon atoms ~200~300 (nanographene 2-3 nm)

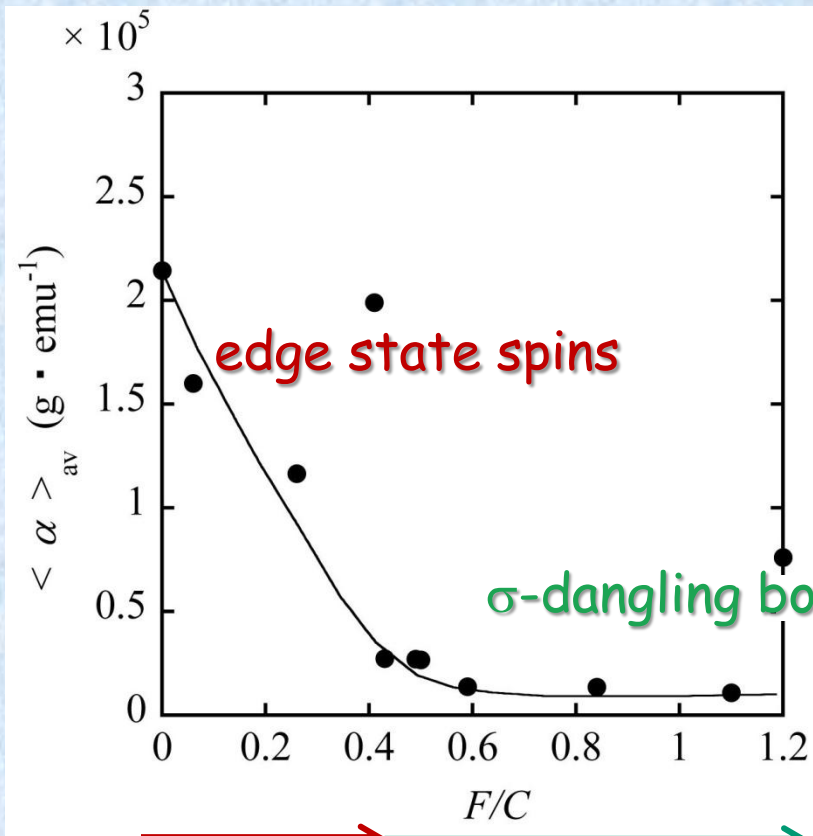


max conc. of dangling bond spins at $F/C \sim 0.8$
 1/2 of interior C atoms fluorinated

edge C interior C fluorinated

magnetism; edge state and σ -dangling bond state

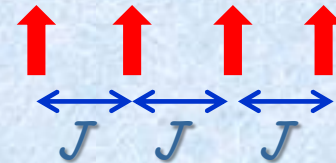
internal exchange field



edge state spins

topological origin

interacting with each other through exchange interaction



σ -dangling bond spins

defect origin

isolated with no interaction



edge C

interior C

fluorinated

Summary

nanographene magnetic

depending on the edge chirality;
zigzag and armchair

edge state of π -electron origin at zigzag edge

σ -dangling bond state at defects

a variety of magnetism

ferromagnetic/antiferromagnetic/ferrimagnetic/spin glass

molecular magnetism & spintronics device applications

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